

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,794,709 B2  
DATED : September 21, 2004  
INVENTOR(S) : Ahn et al.

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page.

Item [56], **References Cited**, U.S. PATENT DOCUMENTS, "4,477,310 A", reference, after "Park et al." insert -- 156 --.

"4,700,212 A", reference, after "Okazawa" insert -- 357 --.

"5,057,449 A", reference, after "Lowrey et al." insert -- 438 --.

"5,257,095 A", reference, after "Liu et al." insert -- 257 --.

"5,731,238 A", reference, after "Cavins et al." insert -- 438 --.

"6,091,109 A", reference, after "Hasegawa" insert -- 257 --.

OTHER PUBLICATIONS, "Guo, X., et al.", reference, delete "TiO<sub>2</sub> Si<sub>3</sub>N<sub>4</sub>" and insert -- TiO<sub>2</sub> Si<sub>3</sub>N<sub>4</sub> --, therefor.

After "Han, I.K., et al.", reference, insert -- Hideo, O., et al., "Dual Gate Oxide Process Integration for High Performance Embedded Memory Products", Extended Abstract of the 1998 International Conference on Solid State Devices and Materials, pp. 108-109, (1998) --.

"Togo, M., et al.", reference, delete "DRAMs" and insert -- DRAMs --, therefor.

Column 5.

Line 40, delete "1999International" and insert -- 1999 International --, therefor.

Column 8.

Lines 14 and 15, delete "SiO<sub>2</sub>" and insert -- SiO<sub>2</sub> --, therefor.

Lines 30 and 33, delete "source drain" and insert -- source/drain --, therefor.

Column 10.

Lines 28, 32, 45, 60 and 64, delete "SiO<sub>2</sub>" and insert -- SiO<sub>2</sub> --, therefor.

Lines 29, 39, 46 and 61, delete "Si<sub>3</sub>N<sub>4</sub>" and insert -- Si<sub>3</sub>N<sub>4</sub> --, therefor.

Column 11.

Lines 21, 25 and 44, delete "SiO<sub>2</sub>" and insert -- SiO<sub>2</sub> --, therefor.

Lines 22, 34 and 49, delete "Si<sub>3</sub>N<sub>4</sub>" and insert -- Si<sub>3</sub>N<sub>4</sub> --, therefor.

Line 49, after "nitride" delete "(Si<sub>3</sub>N<sub>4</sub>)" and insert -- (Si<sub>3</sub>N<sub>4</sub>) --, therefor.

09/943324

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Column 12,

Lines 6, 29 and 50, delete "SiO2" and insert -- SiO<sub>2</sub> --, therefor.

Line 35, delete "Si3N4" and insert -- Si<sub>3</sub>N<sub>4</sub> --, therefor.

Signed and Sealed this

Tenth Day of May, 2005

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JON W. DUDAS  
*Director of the United States Patent and Trademark Office*